



# PJW3N10A

## 100V N-Channel Enhancement Mode MOSFET

**Voltage**

**100 V**

**Current**

**2.2 A**

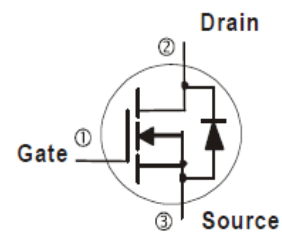
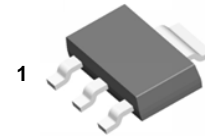
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V, I_D@2.2A < 310m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V, I_D@1A < 320m\Omega$
- Low On-Resistance
- Low input capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

### Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W3N10A

SOT-223



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER                                               |                        | SYMBOL          | LIMIT    | UNITS              |
|---------------------------------------------------------|------------------------|-----------------|----------|--------------------|
| Drain-Source Voltage                                    |                        | $V_{DS}$        | 100      | V                  |
| Gate-Source Voltage                                     |                        | $V_{GS}$        | $\pm 20$ | V                  |
| Continuous Drain Current                                | $T_A=25^\circ\text{C}$ | $I_D$           | 2.2      | A                  |
|                                                         | $T_A=70^\circ\text{C}$ |                 | 1.7      |                    |
| Pulsed Drain Current <sup>(Note 1)</sup>                |                        | $I_{DM}$        | 4.4      | A                  |
| Power Dissipation                                       | $T_A=25^\circ\text{C}$ | $P_D$           | 3.1      | W                  |
|                                                         | $T_A=70^\circ\text{C}$ |                 | 2.0      |                    |
| Operating Junction and Storage Temperature Range        |                        | $T_J, T_{STG}$  | -55~150  | $^\circ\text{C}$   |
| Typical Thermal resistance                              |                        | $R_{\theta JA}$ | 40.3     | $^\circ\text{C/W}$ |
| - Junction to Ambient, $t \leq 10s$ <sup>(Note 5)</sup> |                        |                 |          |                    |

- Limited only By Maximum Junction Temperature



# PJW3N10A

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                                             | SYMBOL              | TEST CONDITION                                                                                        | MIN. | TYP. | MAX. | UNITS |
|-------------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------|------|------|------|-------|
| <b>Static</b>                                         |                     |                                                                                                       |      |      |      |       |
| Drain-Source Breakdown Voltage                        | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                                            | 100  | -    | -    | V     |
| Gate Threshold Voltage                                | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA                                              | 1.0  | 2.06 | 2.5  | V     |
| Drain-Source On-State Resistance                      | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =2.2A                                                            | -    | 284  | 310  | mΩ    |
|                                                       |                     | V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A                                                           | -    | 287  | 320  |       |
| Zero Gate Voltage Drain Current                       | I <sub>DSS</sub>    | V <sub>DS</sub> =80V, V <sub>GS</sub> =0V                                                             | -    | -    | 1.0  | uA    |
| Gate-Source Leakage Current                           | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                                            | -    | -    | ±100 | nA    |
| <b>Dynamic</b> (Note 6)                               |                     |                                                                                                       |      |      |      |       |
| Total Gate Charge                                     | Q <sub>g</sub>      | V <sub>DS</sub> =50V, I <sub>D</sub> =2.2A,<br>V <sub>GS</sub> =10V (Note 1,2)                        | -    | 9.1  | -    | nC    |
| Gate-Source Charge                                    | Q <sub>gs</sub>     |                                                                                                       | -    | 2.1  | -    |       |
| Gate-Drain Charge                                     | Q <sub>gd</sub>     |                                                                                                       | -    | 1.4  | -    |       |
| Input Capacitance                                     | C <sub>iss</sub>    | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,<br>f=1.0MHZ                                                | -    | 508  | -    | pF    |
| Output Capacitance                                    | C <sub>oss</sub>    |                                                                                                       | -    | 29   | -    |       |
| Reverse Transfer Capacitance                          | C <sub>rss</sub>    |                                                                                                       | -    | 18   | -    |       |
| Turn-On Delay Time                                    | t <sub>d(on)</sub>  | V <sub>DD</sub> =50V, I <sub>D</sub> =2.2A,<br>V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω<br>(Note 1,2) | -    | 2    | -    | ns    |
| Turn-On Rise Time                                     | t <sub>r</sub>      |                                                                                                       | -    | 21   | -    |       |
| Turn-Off Delay Time                                   | t <sub>d(off)</sub> |                                                                                                       | -    | 12   | -    |       |
| Turn-Off Fall Time                                    | t <sub>f</sub>      |                                                                                                       | -    | 19   | -    |       |
| <b>Drain-Source Diode</b>                             |                     |                                                                                                       |      |      |      |       |
| Maximum Continuous Drain-Source Diode Forward Current | I <sub>S</sub>      | ---                                                                                                   | -    | -    | 2.2  | A     |
| Diode Forward Voltage                                 | V <sub>SD</sub>     | I <sub>S</sub> =1A, V <sub>GS</sub> =0V                                                               | -    | 0.78 | 1.2  | V     |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature T<sub>J</sub>(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> = 25°C.
5. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



# PJW3N10A

## TYPICAL CHARACTERISTIC CURVES

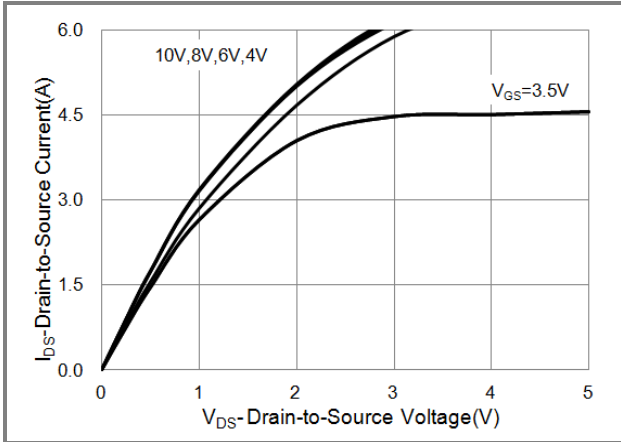


Fig.1 Output Characteristics

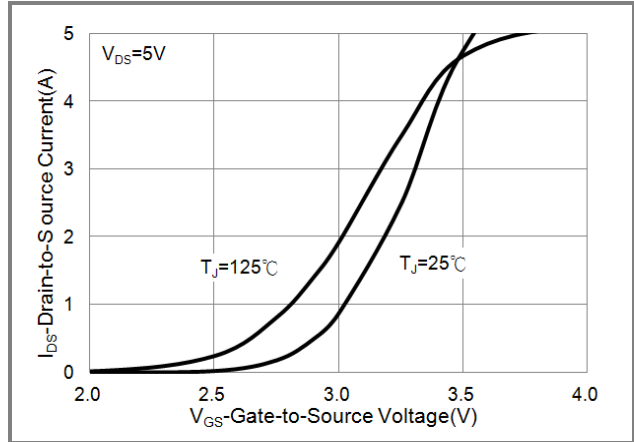


Fig.2 Transfer Characteristics

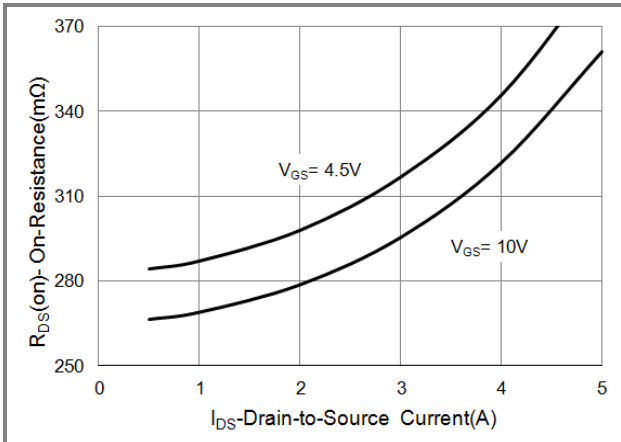


Fig.3 On-Resistance vs. Drain Current

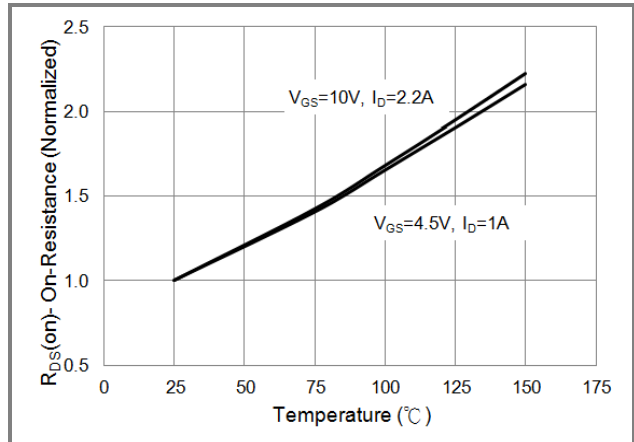


Fig.4 On-Resistance vs. Junction temperature

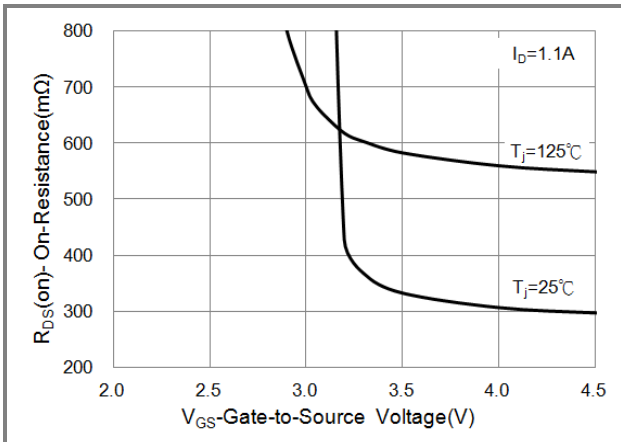


Fig.5 On-Resistance Variation with VGS.

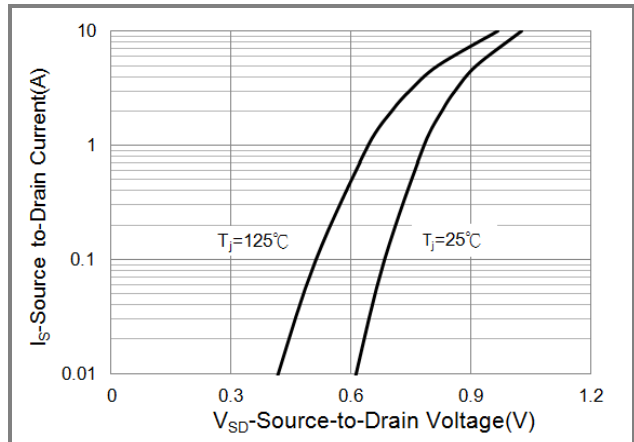


Fig.6 Source-Drain Diode Forward Voltage



# PJW3N10A

## TYPICAL CHARACTERISTIC CURVES

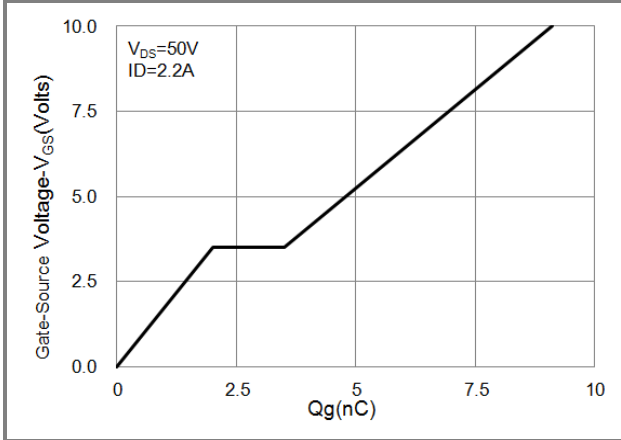


Fig.7 Gate-Charge Characteristics

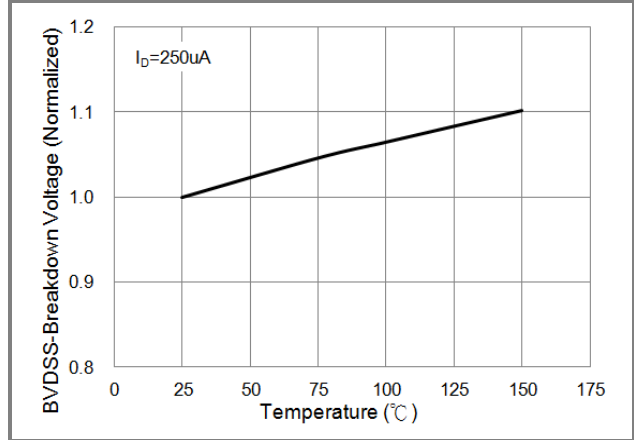


Fig.8 Breakdown Voltage Variation vs. Temperature

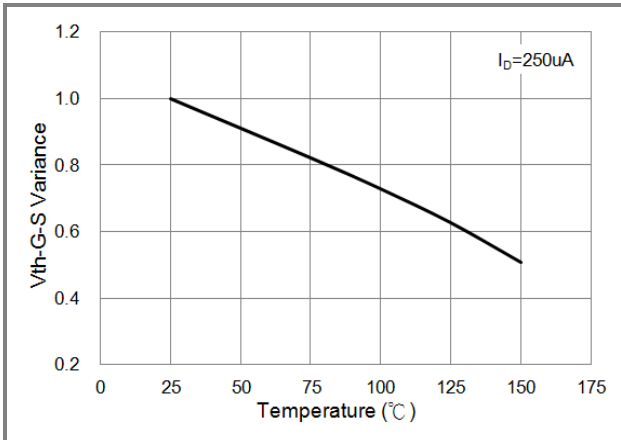


Fig.9 Threshold Voltage Variation with Temperature

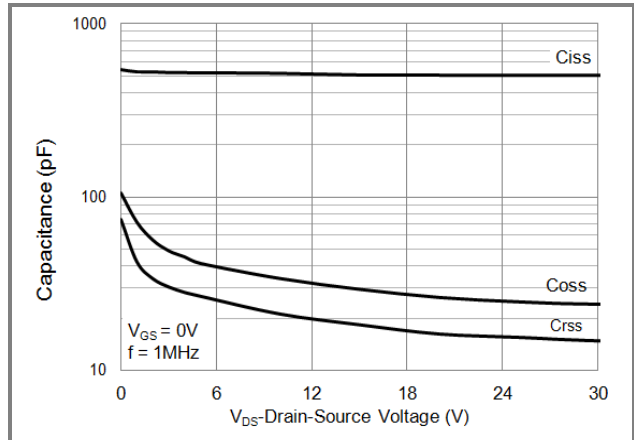


Fig.10 Capacitance vs. Drain-Source Voltage

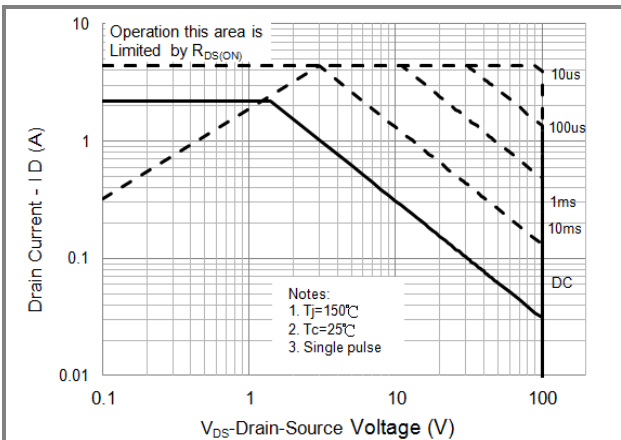


Fig.11 Maximum Safe Operating Area



# PJW3N10A

## TYPICAL CHARACTERISTIC CURVES

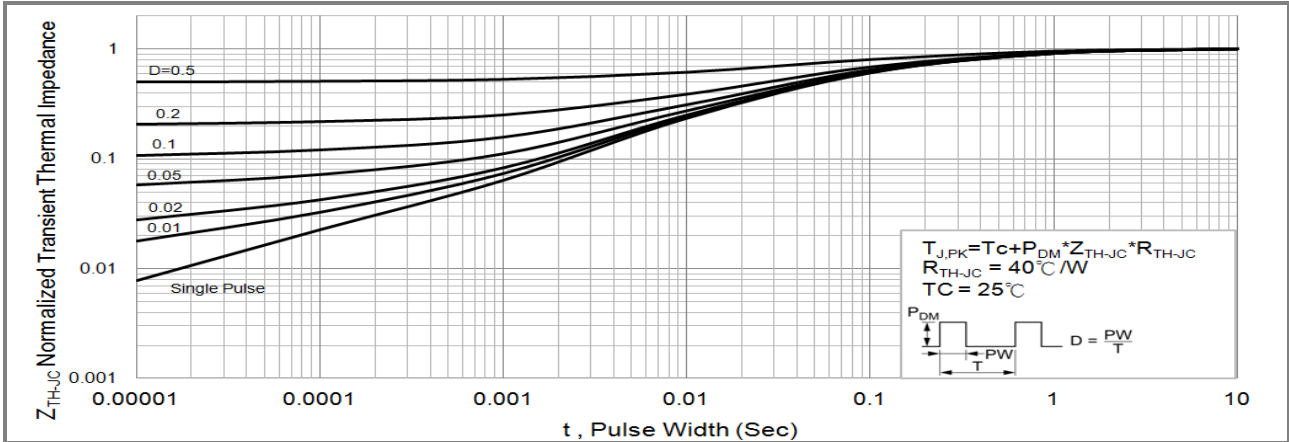
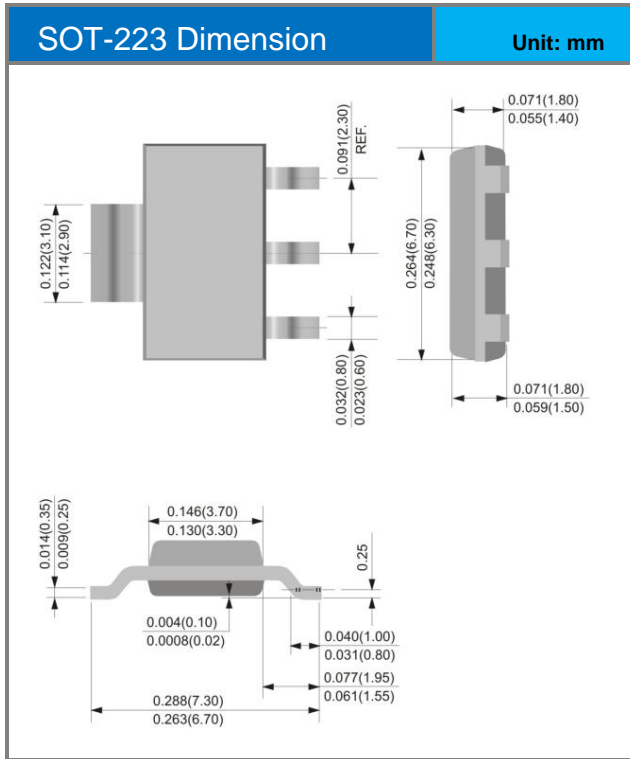


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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## Packaging Information



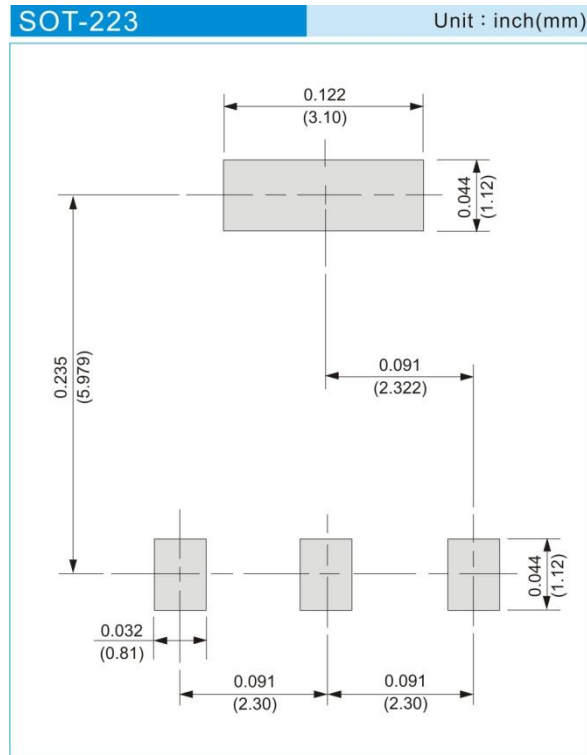


# PJW3N10A

## PART NO PACKING CODE VERSION

| Part No Packing Code | Package Type | Packing type        | Marking | Version      |
|----------------------|--------------|---------------------|---------|--------------|
| PJW3N10A_R2_00001    | SOT-223      | 2.5K pcs / 13" reel | W3N10A  | Halogen free |

## MOUNTING PAD LAYOUT





## PJW3N10A

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